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Substitute for form 1448A/B/PTO				<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use as many sheets as necessary)				Application Number	10/663,741
				Filing Date	September 17, 2003
				First Named Inventor	Terry L. Gilton
				Art Unit	2811
				Examiner Name	Not Yet Assigned
Sheet	1	of	1	Attorney Docket Number	M4065.0656/P656

## U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)			
CS	A	6,673,648	01/06/2004	Lowrey	

## FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>3</sup>
		Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)				

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## NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
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<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached.

296

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# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

## Complete If Known

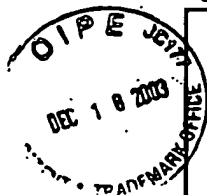
Application Number	10/663,741
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Art Unit	N/A
Examiner Name	Not Yet Assigned
Attorney Docket Number	M4065.0656/P656

Sheet 1 of 11

## U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>1</sup> (if known)			
Ch	AA	2002/0000666	1/3/2002	Kozicki et al.	
Ch	AB	2002/0072188	6/13/2002	Gilton	
Ch	AC	2002/0106849	08/08/2002	Moore	
Ch	AH	2002/0123169	09/05/2002	Moore et al.	
Ch	AI	2002/0123170	09/05/2002	Moore et al.	
Ch	AJ	2002/0123248	09/05/2002	Moore et al.	
Ch	AK	2002/0127886	09/12/2002	Moore et al.	
Ch	AL	2002/0132417	09/09/2002	Li	
Ch	AF	2002/0160551	10/31/2002	Harshfield	
Ch	AG	2002/0163828	11/07/2002	Krieger et al.	
Ch	AM	2002/0168820	11/2002	Kozicki	
Ch	AN	2002/0168852	11/14/2002	Harshfield et al.	
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Ch	AQ	2003/0001229	01/02/2003	Moore et al.	
Ch	AR	2003/0027416	02/06/2003	Moore	
Ch	AS	2003/0032254	02/13/2003	Gilton	
Ch	AT	2003/0035314	02/20/2003	Kozicki	
Ch	AU	2003/0035315	02/20/2003	Kozicki	
Ch	AV	2003/0038301	02/27/2003	Moore	
Ch	AW	2003/0043631	03/06/2003	Gilton et al.	
Ch	AX	2003/0045049	03/06/2003	Campbell et al.	
Ch	AY	2003/0045054	03/06/2003	Campbell et al.	
Ch	AZ	2003/0047765	03/13/2003	Campbell	
Ch	AA1	2003/0047772	03/13/2003	Li	
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Ch	AC1	2003/0048519	03/13/2003	Kozicki	
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Ch	AJ1	2003/0117831	06/26/2003	Hush	
Ch	AK1	2003/0128612	07/10/2003	Moore et al.	
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Ch	AQ1	2003/0156463	08/21/2003	Casper et al.	
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Ch	AS1	3,743,847	7/1973	Boland	
Ch	AT1	4,269,935	5/1981	Masters et al.	

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Sheet	2	of	11
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Ch	AU1	4,312,938	1/1982	Drexler, et al.	
Ch	AV1	4,316,946	1/1982	Masters, et al.	
Ch	AW1	4,320,191	3/1982	Yoshikawa et al.	
Ch	AX1	4,405,710	9/1983	Balasubramanyam et al.	
Ch	AY1	4,419,421	12/1983	Wichelhaus, et al.	
Ch	AZ1	4,499,557	2/1985	Holmberg et al.	
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Ch	AG2	5,238,862	8/1993	Blalock et al.	
Ch	AH2	5,272,359	12/21/1993	Nagasubramanian et al.	
Ch	AI2	5,314,772	5/24/1994	Kozicki	
Ch	AJ2	5,315,131	5/1994	Kishimoto et al.	
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First Named Inventor	Terry L. Gilton
Art Unit	N/A
Examiner Name	Not Yet Assigned
Attorney Docket Number	M4065.0656/P656

Sheet	3	of	11
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<input checked="" type="checkbox"/>	AR3	6,376,284	4/2002	Gonzalez et al.		
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<input checked="" type="checkbox"/>	AF4	2002/0101765	08/01/2002	Mihnea et al.		
<input checked="" type="checkbox"/>	AG4	6,426,898	07/30/2002	Mihnea et al.		
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<input checked="" type="checkbox"/>	AJ4	5,534,712	07/09/1998	Ovshinsky et al.		
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<input checked="" type="checkbox"/>	AL4	2002/0094640	07/18/2002	Forbes		
<input checked="" type="checkbox"/>	AM4	2002/0126533	09/12/2002	Kao		

**FOREIGN PATENT DOCUMENTS**

Examiner Initials*	Cite No.	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>†</sup>
		Country Code <sup>2</sup> -Number <sup>3</sup> -Kind Code <sup>4</sup> (if known)				
<input checked="" type="checkbox"/>	BA	56126916	10/19981	Akira et al.		
<input checked="" type="checkbox"/>	BB	WO 97/48032	12/18/1997	Kozicki et al.		
<input checked="" type="checkbox"/>	BC	WO 99/28914	06/10/1999	Kozicki et al.		
<input checked="" type="checkbox"/>	BD	WO 00/48196	08/17/2000	Kozicki et al.		
<input checked="" type="checkbox"/>	BE	WO 02/21542	03/14/2002	Kozicki et al.		

Examiner Signature	<i>[Signature]</i>	Date Considered	12-12-04
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# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet	4	of	11
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## Complete if Known

Application Number	10/663,741
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First Named Inventor	Terry L. Gilton
Group Art Unit	N/A
Examiner Name	Not Yet Assigned
Attorney Docket Number	M4065.0656/P656

## OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
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an	CB	Adler, D.; Moss, S.C., Amorphous memories and bistable switches, J. Vac. Sci. Technol. 9 (1972) 1182-1189.	
an	CC	Adler, D.; Henisch, H.K.; Mott, S.N., The mechanism of threshold switching in amorphous alloys, Rev. Mod. Phys. 50 (1978) 209-220.	
an	CD	Afifi, M.A.; Labib, H.H.; El-Fazary, M.H.; Fadel, M., Electrical and thermal properties of chalcogenide glass system Se <sub>75</sub> Ge <sub>25-x</sub> Sb <sub>x</sub> , Appl. Phys. A 55 (1992) 167-169.	
an	CE	Afifi, M.A.; Labib, H.H.; Fouad, S.S.; El-Shazly, A.A., Electrical & thermal conductivity of the amorphous semiconductor GexSe <sub>1-x</sub> , Egypt, J. Phys. 17 (1986) 335-342.	
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an	CP	Benmore, C.J.; Salmon, P.S., Structure of fast ion conducting and semiconducting glassy chalcogenide alloys, Phys. Rev. Lett. 73 (1994) 264-267.	
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Substitute for form 1448B/PTO

INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet	5	of	11
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# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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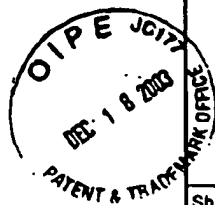
Sheet	7	of	11	Attorney Docket Number	M4065.0656/P656
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Sheet	9	of	11
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Examiner Signature	<i>[Signature]</i>	Date Considered	12-12-04
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				Application Number	10/663,741-Conf. #2658
				Filing Date	September 17, 2003
				First Named Inventor	Terry L. Gilton
				Art Unit	2811
				Examiner Name	Not Yet Assigned
				Attorney Docket Number	M4065.0656/P656
Sheet	1	of	1		

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Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)			

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		Country Code <sup>4</sup> -Number <sup>5</sup> -Kind Code <sup>6</sup> (if known)				

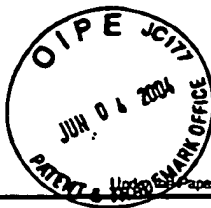
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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
an	CA	YOJI KAWAMOTO et al., "Ionic Conduction in As <sub>2</sub> S <sub>3</sub> -Ag <sub>2</sub> S, GeS <sub>2</sub> -GeS <sub>2</sub> -GeS-Ag <sub>2</sub> S and P <sub>2</sub> S <sub>5</sub> -Ag <sub>2</sub> S Glasses," Journal of Non-Crystalline Solids 20 (1976) 393-404.	

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*Handwritten date: 12-12-04*



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		Filing Date	September 17, 2003
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		Art Unit	2811
		Examiner Name	Not Yet Assigned
Sheet	1	of	3
		Attorney Docket Number	M4065.0656/P656

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		Number-Kind Code <sup>2</sup> (if known)			
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			Filing Date	September 17, 2003	
			First Named Inventor	Terry L. Gilton	
			Art Unit	2811	
			Examiner Name	Not Yet Assigned	
Sheet	2	of	3	Attorney Docket Number	M4065.0656/P656

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Sheet	3	of	3	Attorney Docket Number	M4065.0656/P656

<i>Ch</i>	R3	US 6,646,297	11/2003	Dennison	
<i>Ch</i>	S3	US 6,649,928	11/2003	Dennison	
<i>Ch</i>	T3	US 6,667,900	12/2003	Lowery et al.	
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<i>Ch</i>	V3	US 6,673,700	1/2004	Dennison et al.	
<i>Ch</i>	W3	US 6,674,115	1/2004	Hudgens et al.	
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<i>Ch</i>	Z3	US 6,696,355	2/2004	Dennison	
<i>Ch</i>	A4	US 6,687,153	2/2004	Lowery	
<i>Ch</i>	B4	US 6,707,712	3/2004	Lowery	
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